

Proposed

RF3800

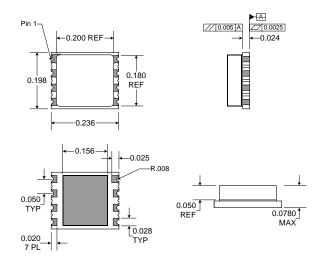
GaAs HBT PRE-DRIVER AMPLIFIER

Typical Applications

- Pre-Driver for 450 MHz Basestation Amplifiers
- PA Stage for Commercial Wireless Infrastructure
- Class AB Operation for Cellular Radio and Wireless Local Loop

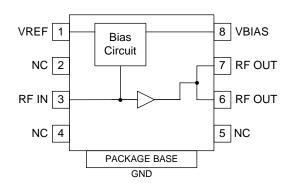
Product Description

The RF3800 is specifically designed for wireless infrastructure applications in 450MHz. Using a highly reliable GaAs HBT fabrication process, this high-performance single-stage amplifier achieves high output power over a broad frequency range. The RF3800 also provides excellent efficiency and thermal stability through the use of a thermally-enhanced surface-mount AIN package. Ease of integration is accomplished through the incorporation of an optimized evaluation board design provided to achieve proper 50 Ω operation. Various evaluation board bias configurations are available to address a broad range of wireless infrastructure applications.



Optimum Technology Matching® Applied

🗌 Si BJT	GaAs HBT	GaAs MESFET
Si Bi-CMOS	SiGe HBT	Si CMOS
InGaP/HBT	GaN HEMT	SiGe Bi-CMOS



Functional Block Diagram

Package Style: AIN

Features

- 6W Output Power
- High Linearity
- 45% Power-Added Efficiency
- Thermally-Enhanced Packaging
- Broadband Platform Design Approach

Ordering Information

RF3800 GaAs HBT Pre-Driver Amplifier RF3800PCBA-416 Fully Assembled Evaluation Board

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RF3800

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